

innovations
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Design of Fully Differential OpAmps for GHz Range Applications

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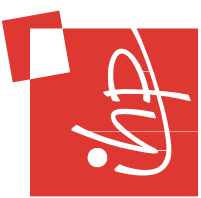
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- **Motivation**
- **Influence of delay on OpAmp Stability**
- **Comparison PNP/NPN with BiCMOS RF OpAmp**
- **Low voltage PNP/NPN OpAmp topology**
- **Simulation results**
- **Conclusions**

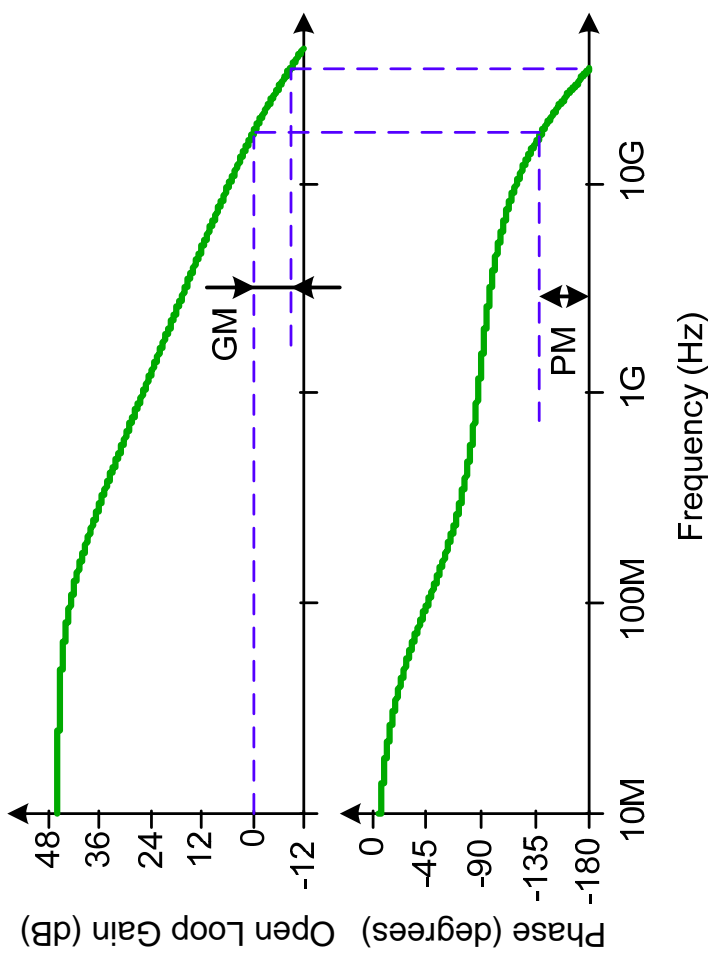
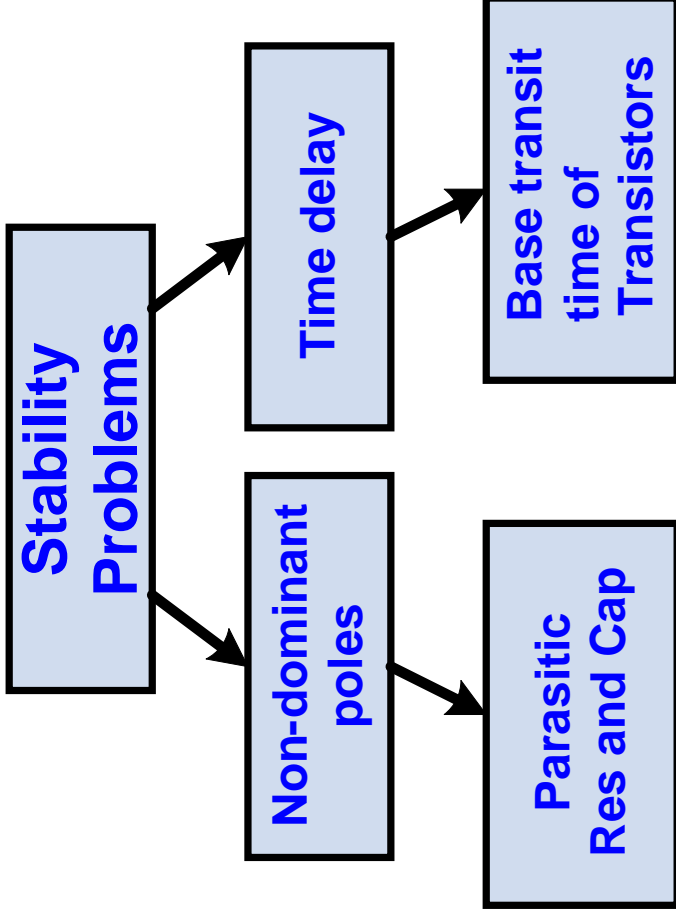
Motivation

- OpAmps are frequently used as RF blocks of Communication system in **MHz range**
- It is attractive to extend OpAmp operation frequencies to **GHz range**
- The main OpAmp parameters for design RF blocks are Unity Gain Bandwidth (UGB) and Phase Margin (PM)
- Topologies comparison and development required

Stability of an OpAmp

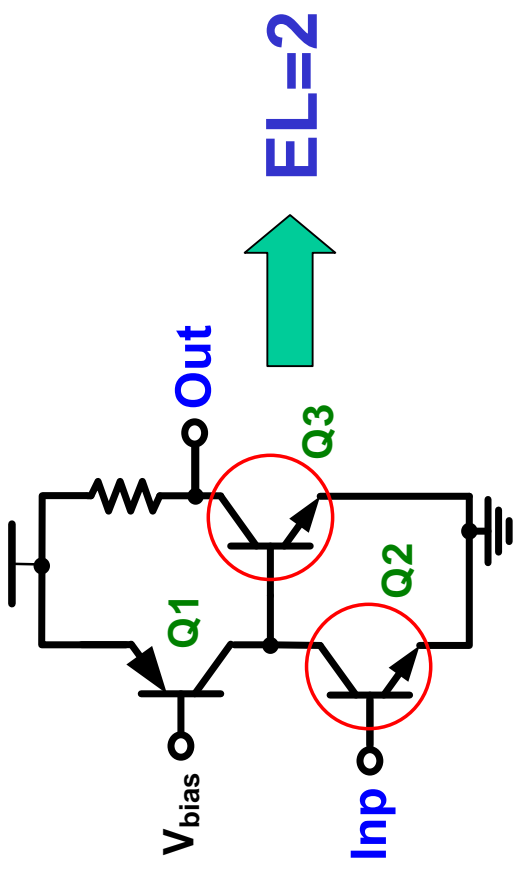
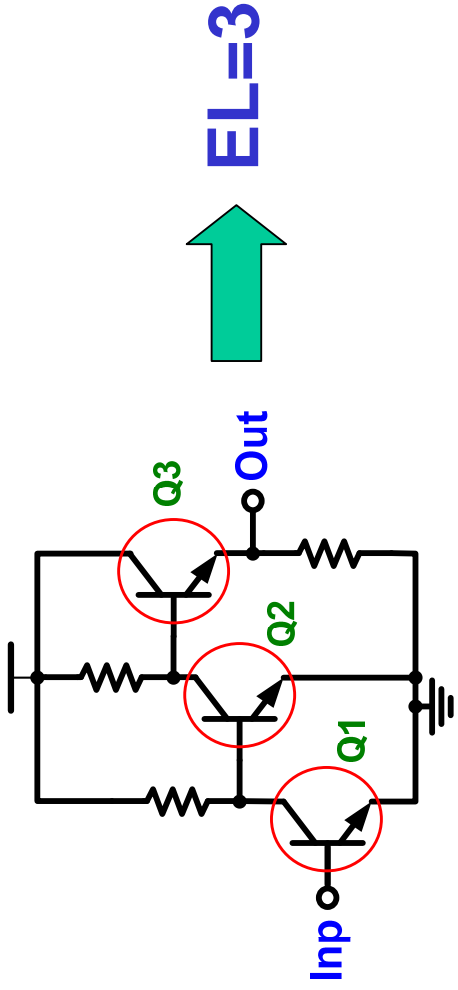
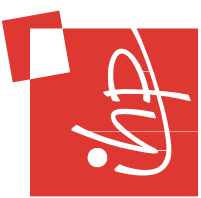


To build up an RF block (amplifier, filter and etc.) we introduce a negative feedback and **stability issue arises**



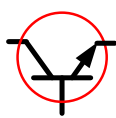
In case the feedback factor of unity, to get stable operation we have to satisfy conditions **PM>45 degrees** and **GM>6dB**

"Electrical Length"

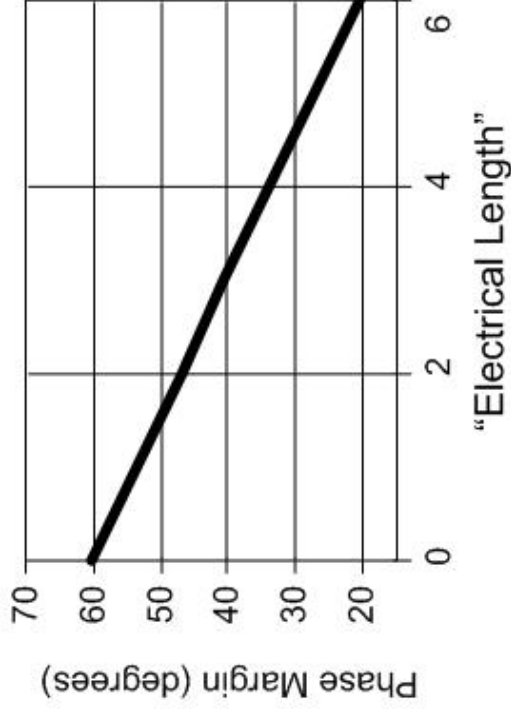
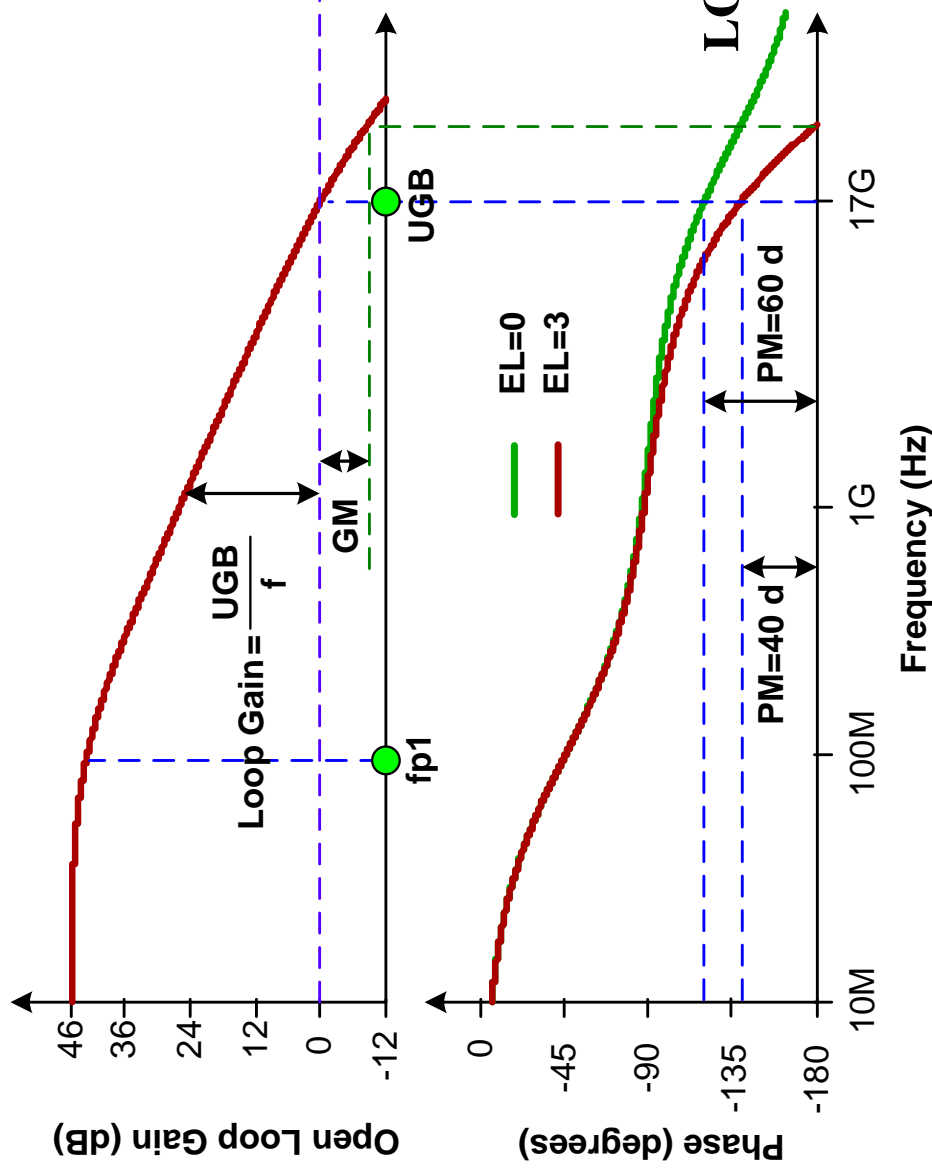
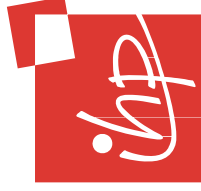


$$\text{Delay time is } EL \cdot \frac{1}{\omega_T} = EL \cdot \tau_B$$

"Electrical Length" is the number of transistors taking part in the signal processing



Delay influence on Phase Margin



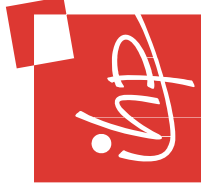
$$|B| = \frac{A_{OL}}{B} = \frac{UGB}{f}$$

$fp1 > f > UGB$

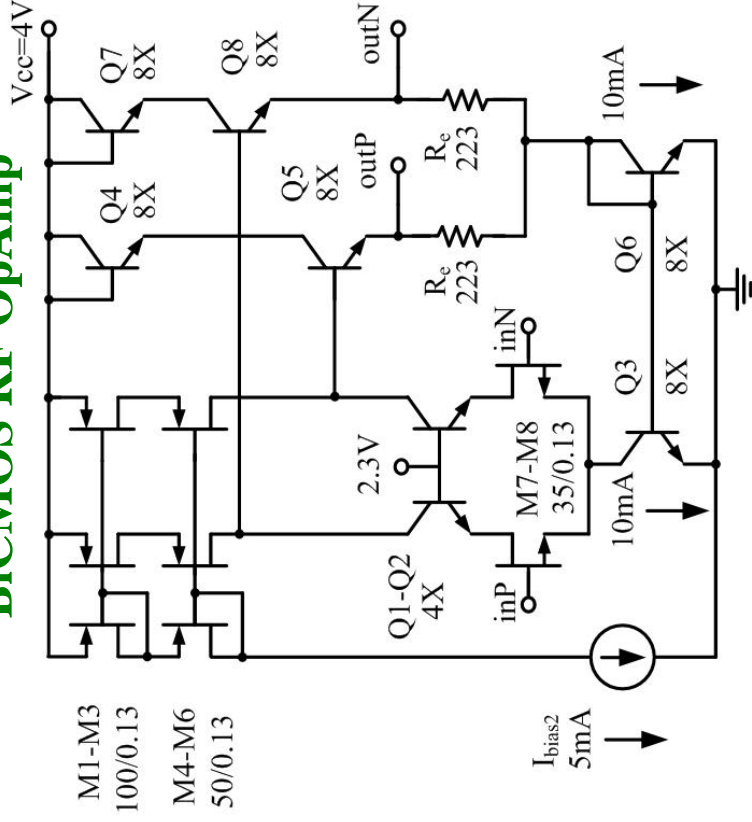
Roll Off=20dB/dec

$$A_{OL} = \frac{200}{(1+s/2\pi \cdot 100 \cdot 10^6)(1+s/2\pi \cdot 30 \cdot 10^9)} \cdot e^{-s \cdot EL/2\pi \cdot 150 \cdot 10^9}$$

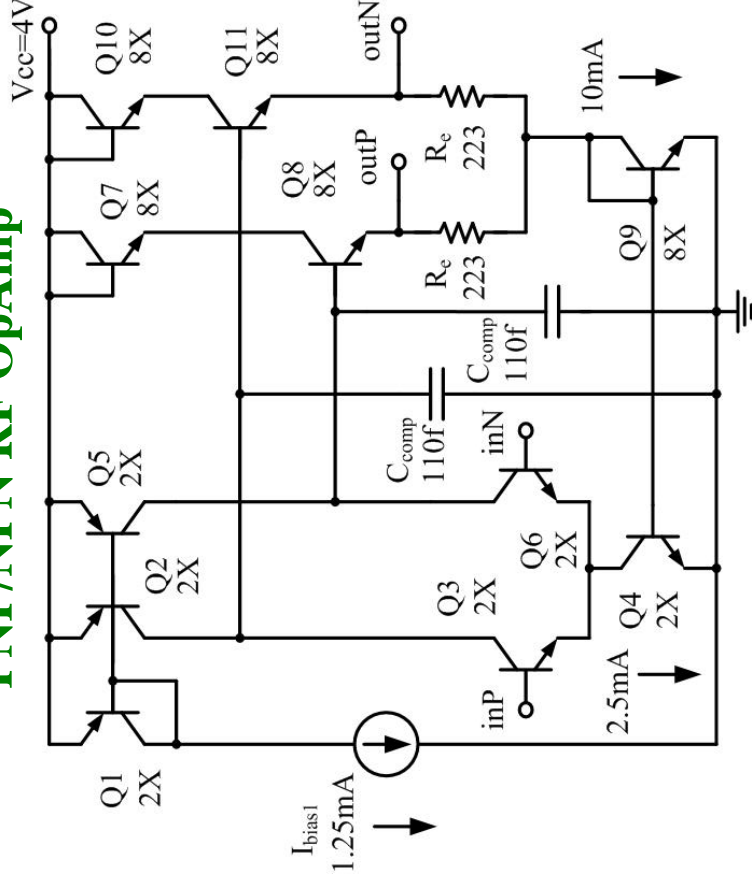
Comparison PNP/NPN with BiCMOS RF OpAmp



BiCMOS RF OpAmp



PNP/NPN RF OpAmp



$$C_{inP}=C_{gs}=WLC_{ox}$$

$$EL=3$$

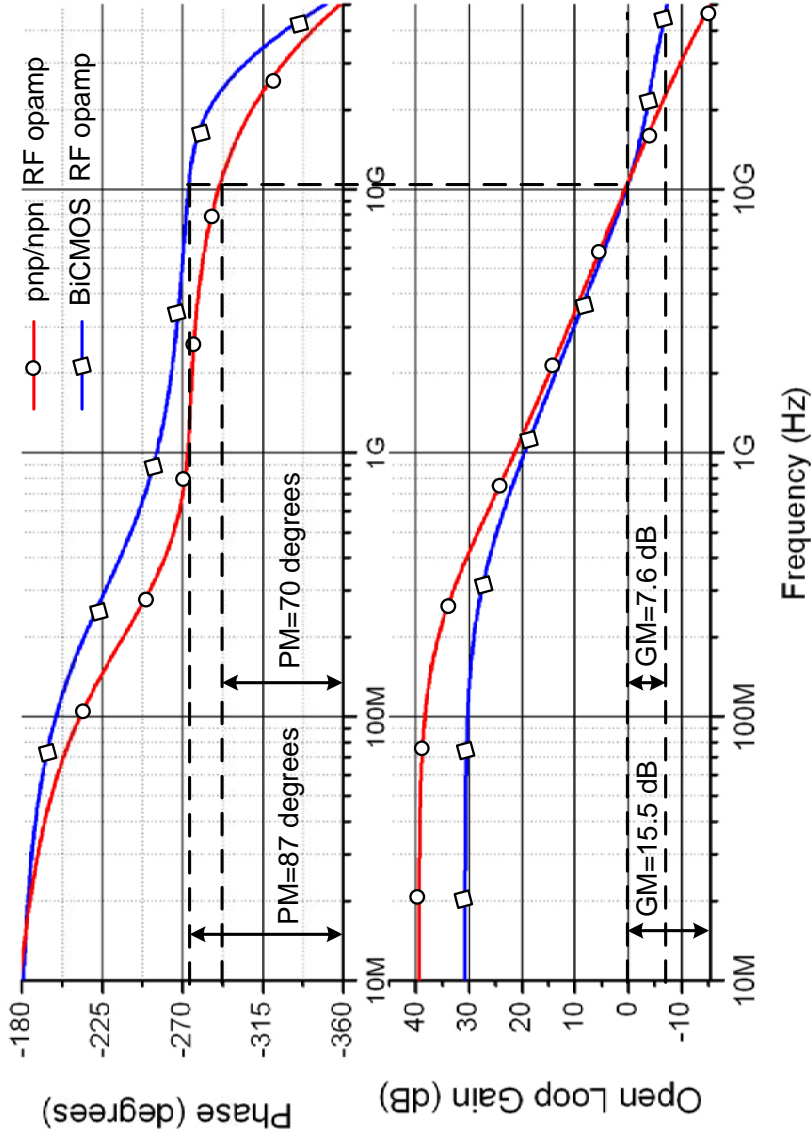
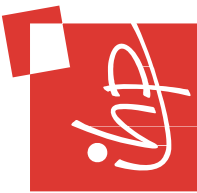
$$C_{inP}=C_{be}=\tau_b \frac{I_e}{V_T}$$

$$EL=2$$

S.P. Voinigescu, et al., "Design Methodology and Applications of SiGe BiCMOS Cascode Opamps with up to 37-GHz Unity Gain Bandwidth," IEEE CSICS, Techn. Digest, pp.283-286, Nov. 2005.

This work

Comparison PNP/NPN with BiCMOS RF OpAmp

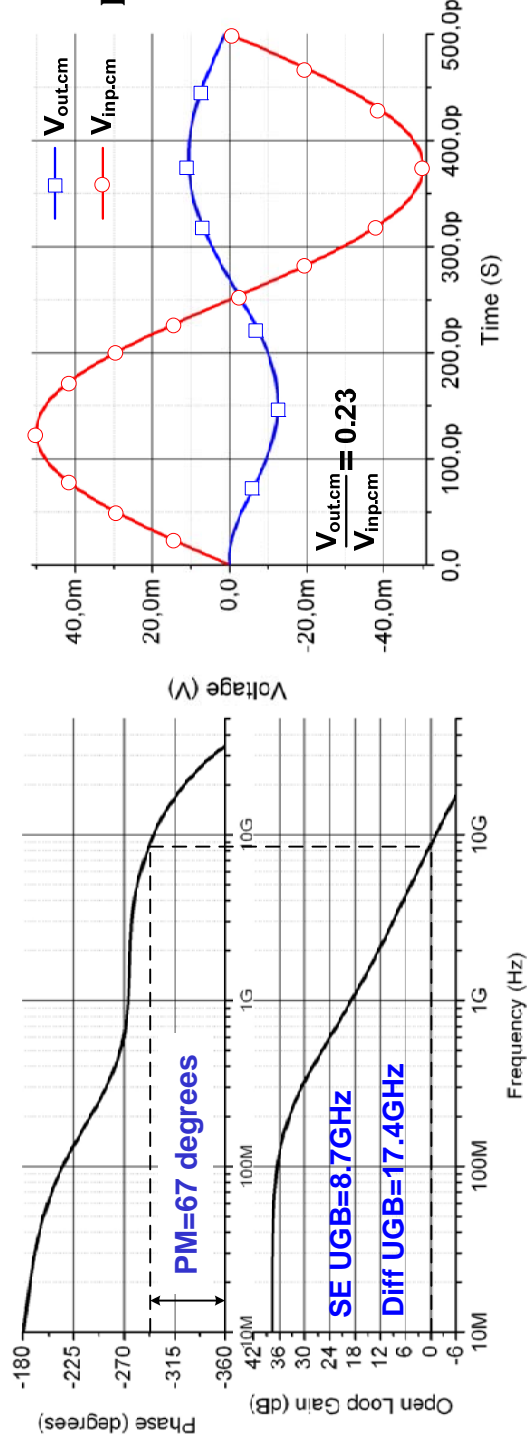


BiCMOS OpAmp has better
PM=87 degrees and
PNP/NPN OpAmp has better
GM=15 dB

The MOSFET models of
BiCMOS OpAmp are
preliminary

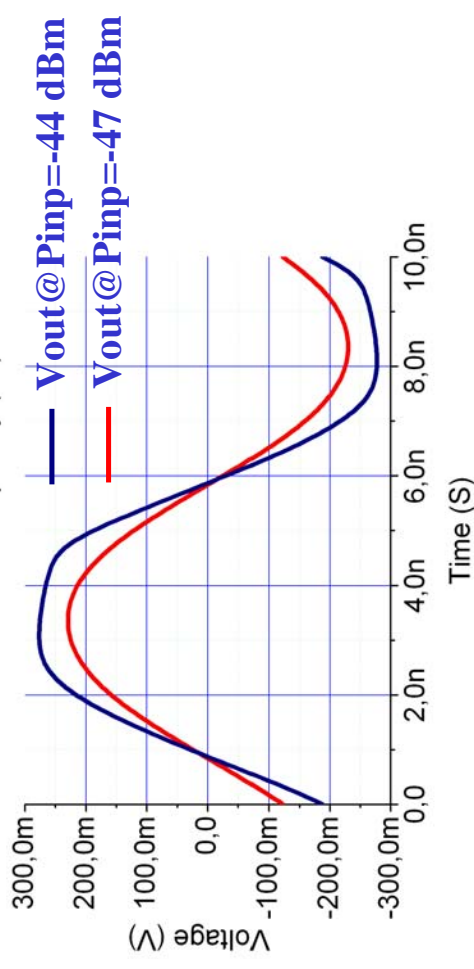
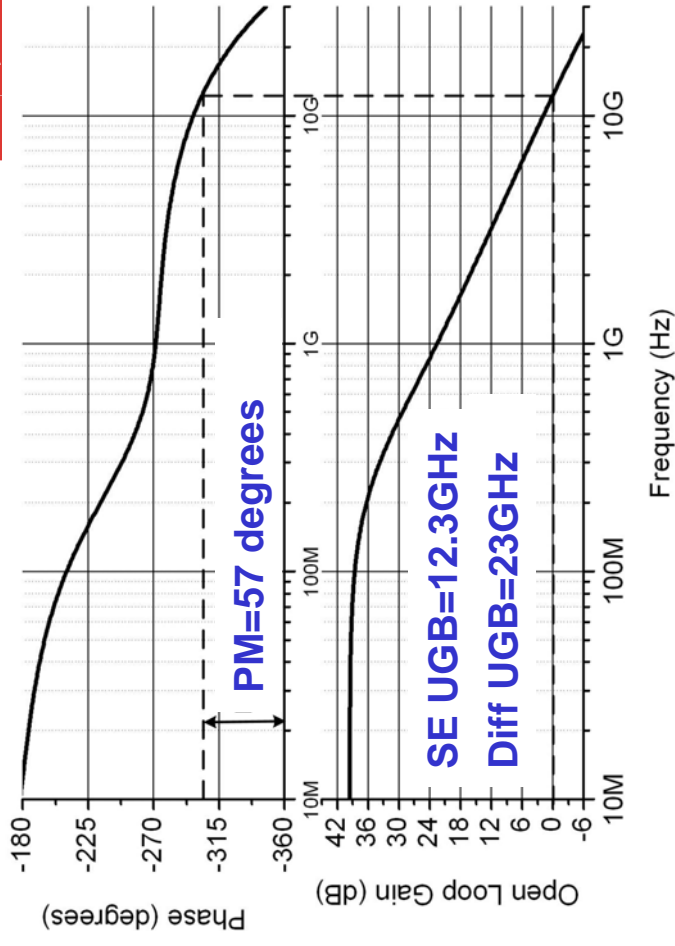
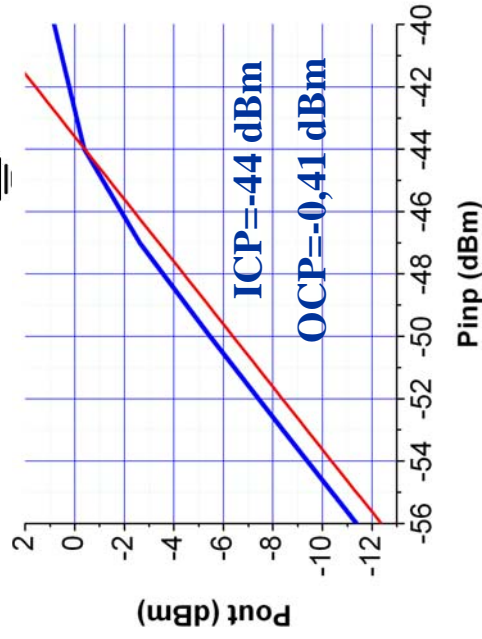
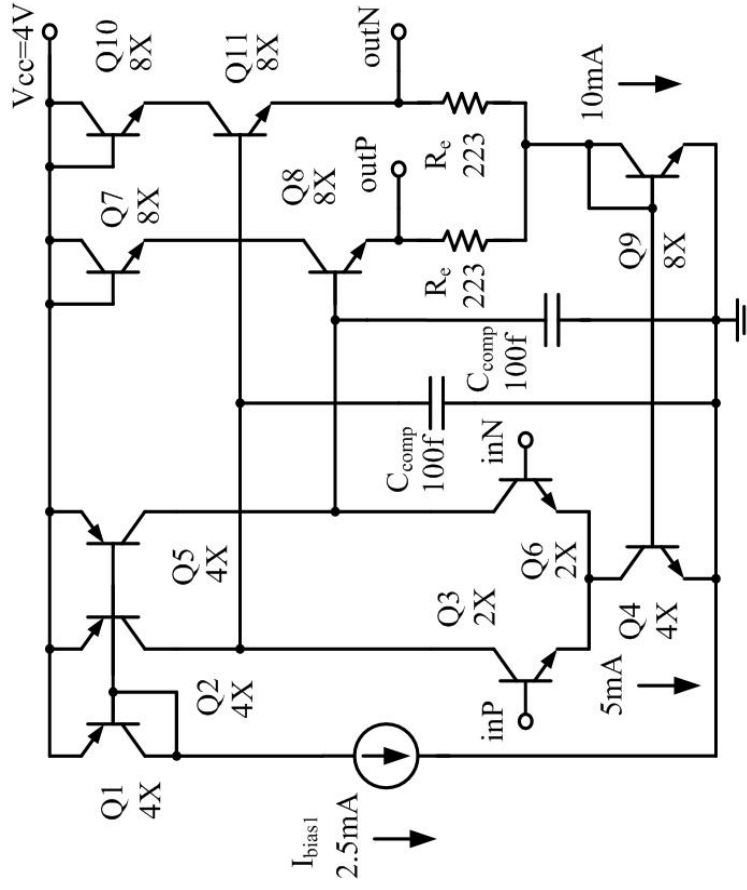
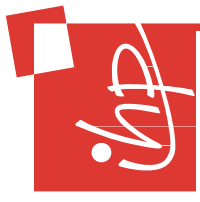
The Supply Voltage of the
OpAmps is 4 V

RF opamp	Parameters and Units			
	SE U_{GB} , GHz	PM, degrees	GM, dB	DC Gain, dB
PNP/NPN	10.7	70	-15.5	39.4
BiCMOS	10.7	87	-7.6	30.8

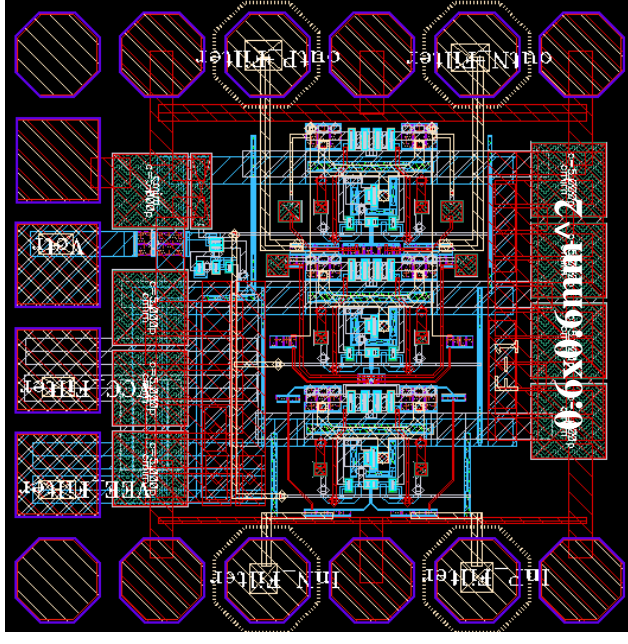
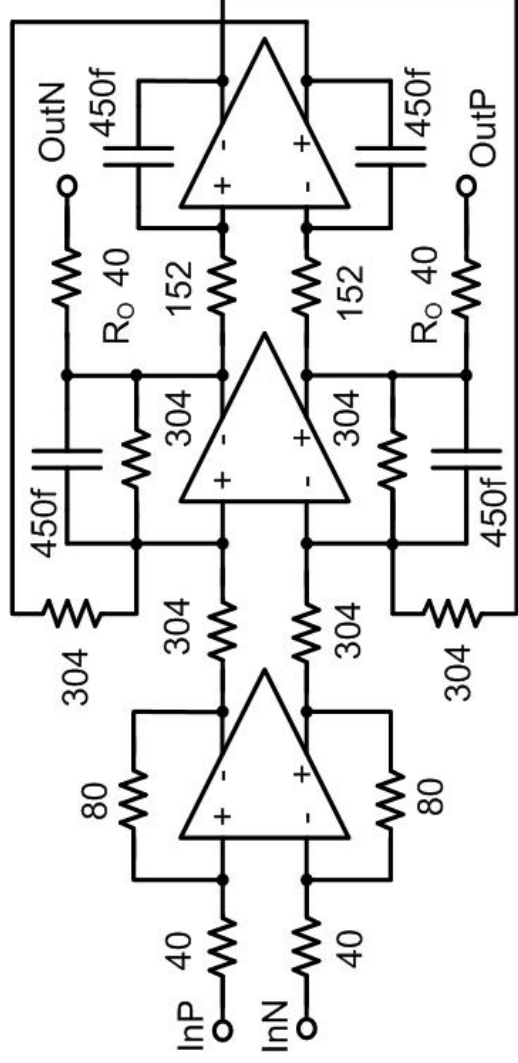


Diff V_{out}=890 mVp-p

Characteristics of the PNP/NPN OpAmp

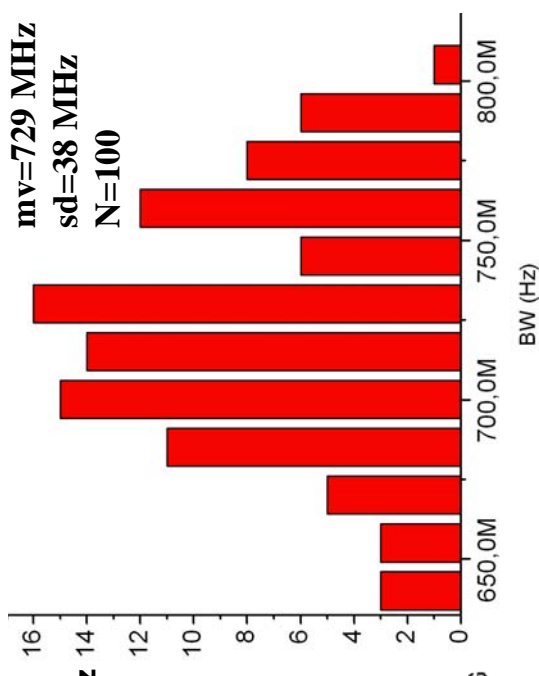
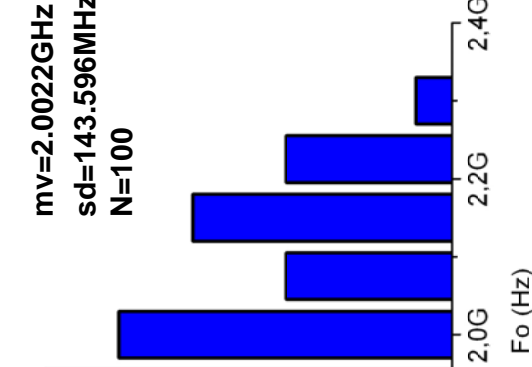
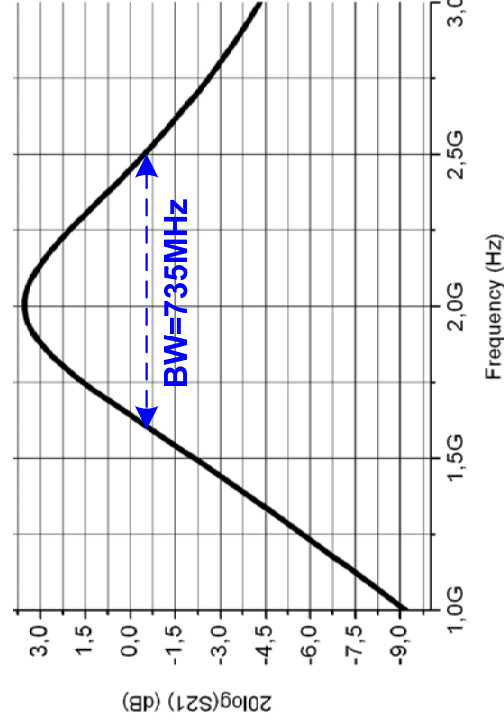


2GHz bandpass Filter

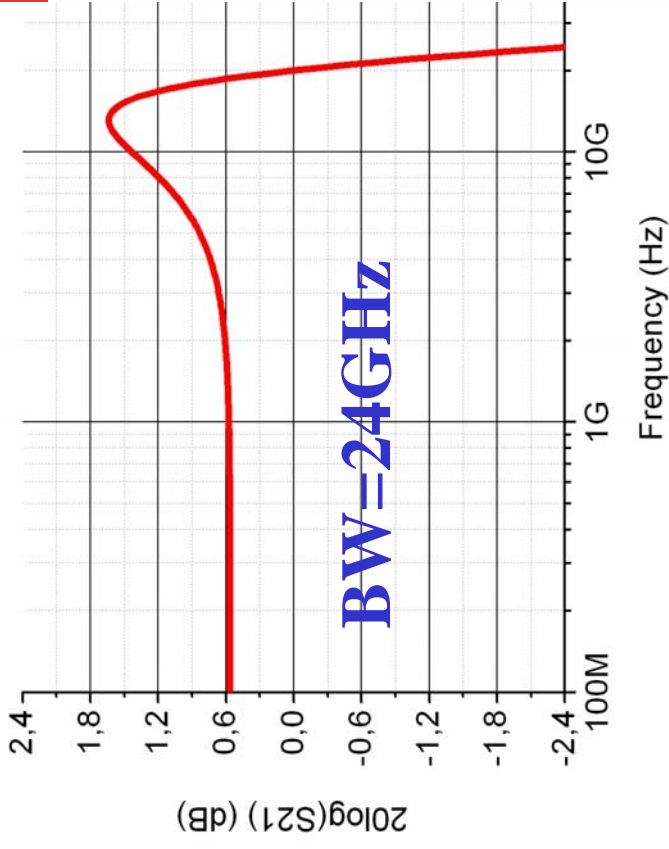
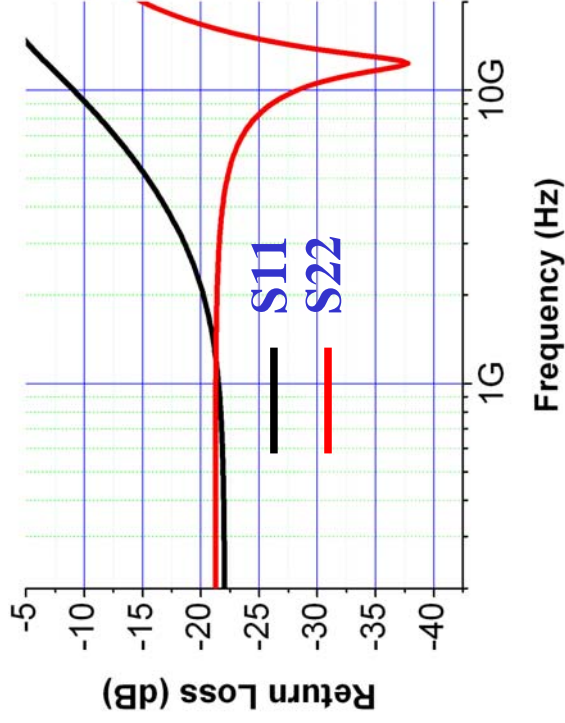
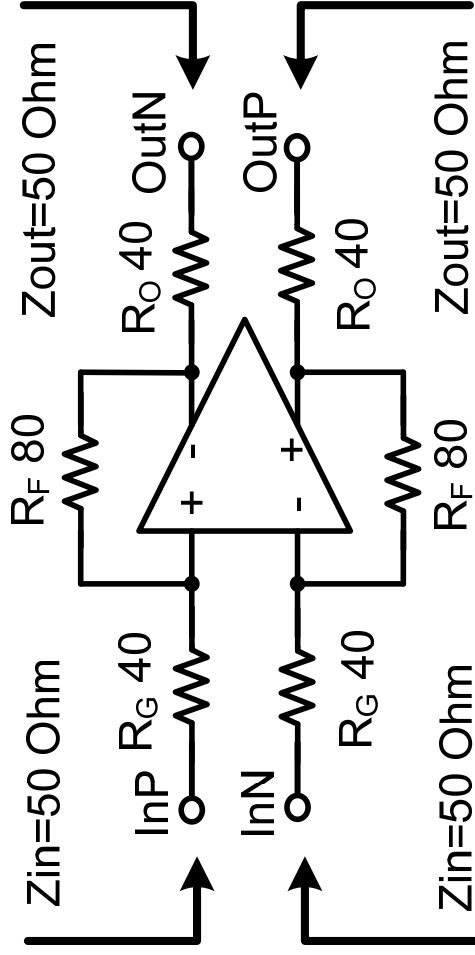


Buffer 1st Integrator 2nd Integrator

ICP=-7dBm OCP=-4.3dBm NF=21.6dB



Line Driver



OCP=-3.2dBm

V_{out,max}=430mVp-p

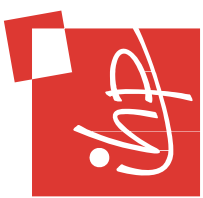
NF=12.5 dB

$$Z_{in} = R_G + \frac{R_F}{LG} \quad LG > > 1 \Rightarrow R_G$$

LG degrades with frequency. That's why input return loss degrades at high frequency where LG is too small

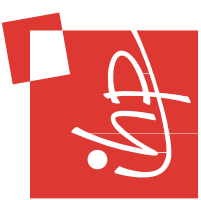
Conclusions

- An RF OpAmp for GHz-range applications with unity feedback should be realized with minimum “Electrical Length” circuit for stable operation
- BiCMOS and PNP/NPN RF OpAmp topologies comparison has been presented. Appropriate topology can be chosen according to the application requirements (**consumption current, supply voltage, DC open loop gain, cost**)
- A low voltage RF OpAmp topology has been presented for supply voltage 3 V
- Application of RF OpAmp for design of a 2G bandpass Filter and a Line Driver with BW=24GHz has been demonstrated

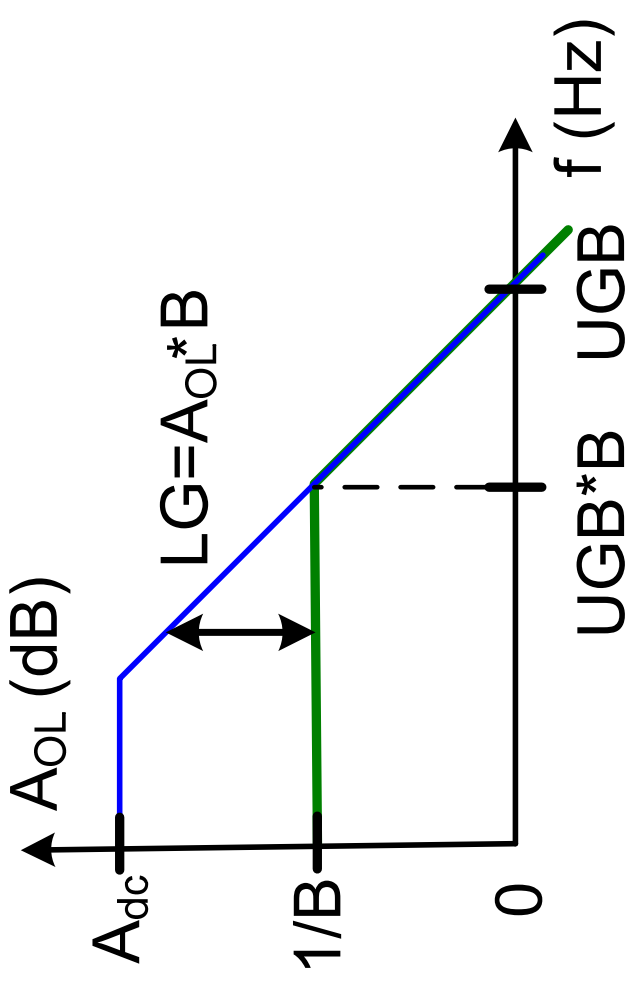
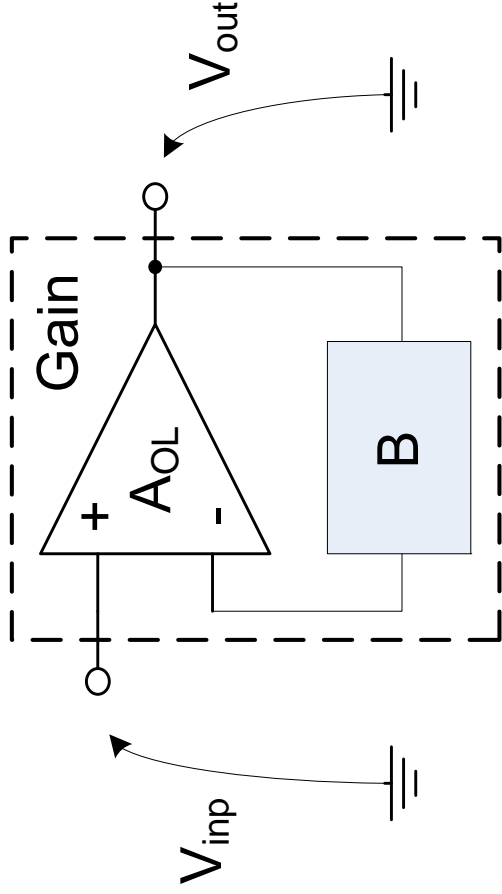


THANK YOU!!

Signal Conditioning Accuracy



$$\text{Gain} = \frac{LG}{LG+1} \cdot \frac{1}{B} \quad \left| \approx \frac{1}{B} \right|_{LG \gg 1}$$



For $B=1$ $\rightarrow LG = \frac{UGB}{f_s}$ $\rightarrow UGB$ should be a few times higher than f_s